

Notice of References Cited	Application/Control No. 09/867,662	Applicant(s)/Patent Under Reexamination OUELLET ET AL.	
	Examiner Brian K Talbot	Art Unit 1762	Page 1 of 1

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NON-PATENT DOCUMENTS

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	U	Hsieh et al., "Characteristics of low-temperature and low-energy plasma-enhanced chemical vapor deposited SiO ₂ ", Journal Applied Physics 74 (4), 15 August 1993, pp. 2638-2648.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.